

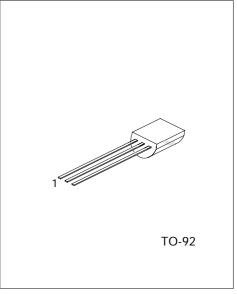
UTC UNISONIC TECHNOLOGIES CO.,LTD.

XL/ML1225

MEDIUM POWER LOW VOLTAGE TRANSISTOR

DESCRIPTION

The XL1225/ML1225 silicon controlled rectifiers are high performance planner diffused PNPN devices. These parts are intended for low cost high volume applications.



*Pb-free plating product number: XL1225L/ML1225L

PIN CONFIGURATION

PIN NO.	PIN NAME
1	CATHODE
2	GATE
3	ANODE

ORDERING INFORMATION

Order Number		Package	Packing	
Normal	Lead free	Fackage	Facking	
XL1225-T92-B	XL1225L-T92-B	TO-92	Tape Box	
XL1225-T92-K	XL1225L-T92-K	TO-92	Bulk	
ML1225-T92-B	ML1225L-T92-B	TO-92	Tape Box	
ML1225-T92-K	ML1225L-T92-K	TO-92	Bulk	

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PARAMETER		SYMBOL	TEST CONDITION	RATINGS	UNIT
Repetitive Peak	XL1225	V _{DRM}	T _J =40 ~ 125°C	400	V
Off-State Voltage	ML1225	V DRM	R _{GK} =1kΩ	300	v
On-State Current		I _{T(RMS)}	Tc=40°C	0.8	А
Average On-State Cu	irrent	I _{T(AV)}	Half Cycle=180,Tc=40°C	0.5	А
Peak Reverse Gate V	/oltage	V_{GRM}	IGR=10uA	1	V
Peak Gate Current		I _{GM}	10us Max.	0.1	А
Gate Dissipation		P _{G(AV)}	20ms Max.	150	mW
Operating Temperatu	ire	TJ		+125	°C
Storage Temperature	•	T _{STG}		-40 ~ +150	°C

■ ABSOLUATE MAXIUM RATINGS (Ta= 25 , unless otherwise specified)

Note 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. The device is guaranteed to meet performance specification within 0 \sim 70 operating temperature range and assured by design from -20 \sim 85.

■ ELECTRICAL CHARACTERISTICS (Ta= 25 , unless otherwise specified.)

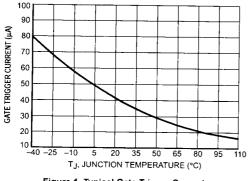
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Off State Leakage Current	IDRM	@V _{DRM} (R _{GK} =1KΩ), T _J =125°C			0.1	mA	
Off State Leakage Current	I _{DRM}	@V _{DRM} (R _{GK} =1KΩ), T _J =25°C			1.0	μA	
On State Voltage	VT	AT I⊤=0.4A			1.4	V	
	VI	AT I _T =0.8A			2.2	v	
On State Threshold Voltage	V _{T(TO)}	T _J =125°C			0.95	V	
On State Slops Resistance	Rt	T _J =125°C			600	m	
Gate Trigger Current	I _{GT}	V _D =7V			200	μA	
Gate Trigger Voltage	V _{GT}	V _D =7V			0.8	V	
Holding Current	Ι _Η	R _{GK} =1KΩ			5	mA	
Latching Current	١L	R _{GK} =1KΩ			6	mA	
Critical Rate of Voltage Rise	DV/DT	$V_{D}=0.67^{*}V_{DRM}(R_{GK}=1K\Omega), T_{J}=125$				V/µs	
Critical Rate of Current Rise	DV/DT	I _G =10mA, dI _G /dt=0.1A/μs,T _J =125				A/μs	
Gate Controlled Delay Time	T_{GD}	l _G =10mA, dl _G /dt=0.1A/μs			2.2	μs	
Commutated Turn-off Time		T _J =85°C, V _D =0.67*V _{DRM} V _R =35V, I _T =I _{T(AV)}			200	μs	

■ CLASSIFICATION OF I_{GT}

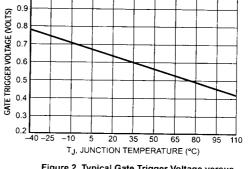
RANK	В	С	AA	AB	AC	AD
RANGE	50-100μA	100-200μA	8-15μA	15-20μA	20-25µA	25-50μA



TYPICAL CHARACTERICS







1.0

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

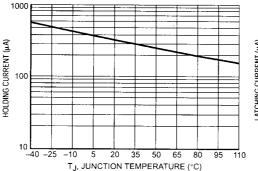


Figure 3. Typical Holding Current versus Junction Temperature

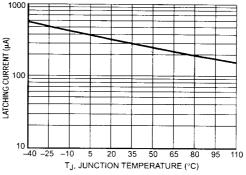
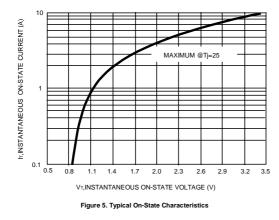


Figure 4. Typical Latching Current versus Junction Temperature



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